

Junction Diode

Lecture - 6

(05/06/2021)

B.Sc (Electronics)
TDC PART - I
Paper – 1 (Group – B)
Unit – 5
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Barrier Width and Junction Capacitance of Contact Potential Across the P-N Junction (PART – 2)

(B) Barrier Width

⇒ The **Space Charge Region** has a **width** equal to,

$$X = X_1 + X_2 \dots\dots\dots (19)$$

⇒ Now putting the value of X_1 and X_2 of Equation (17) and Equation (18) from

Lecture - 5 to the above Equation (19), then we get,

$$X = \left[\frac{2 \epsilon V_B}{e N_a \left(1 + \frac{N_a}{N_d} \right)} \right]^{\frac{1}{2}} + \left[\frac{2 \epsilon V_B}{e N_d \left(1 + \frac{N_d}{N_a} \right)} \right]^{\frac{1}{2}} \dots\dots\dots (20)$$

$$X = \left(\frac{2 \epsilon V_B}{e} \right)^{\frac{1}{2}} \left[\left\{ \frac{N_d/N_a}{N_a + N_d} \right\}^{\frac{1}{2}} + \left\{ \frac{N_a/N_d}{N_a + N_d} \right\}^{\frac{1}{2}} \right] \dots\dots\dots (21)$$

$$\therefore X = \left[\frac{2 \epsilon V_B}{e (N_a + N_d)} \right]^{\frac{1}{2}} \left[\left(\frac{N_d}{N_a} \right)^{\frac{1}{2}} + \left(\frac{N_a}{N_d} \right)^{\frac{1}{2}} \right] \dots\dots\dots (22)$$

❖ **Example :-** Consider a typical example with,

- ✦ $N_d \approx N_a \approx 10^{21}$ per m^3
- ✦ $V_B = 0.5$ volt
- ✦ $\epsilon_0 = 8.85 \times 10^{-12}$ farad / meter,
- ✦ $\epsilon_r = 16$ for Ge (**Germanium**)

⇒ So, we know that, $\epsilon = \epsilon_0 \cdot \epsilon_r$

- ✦ $\epsilon = 8.85 \times 10^{-12} \times 16$ farad / meter (**for Ge**) and
- ✦ $e = 1.6 \times 10^{-19}$ coulomb

⇒ Now putting the above values of **different parameters** in above **Equation (22)**, then we find that the **Width (Thickness) of Junction Barrier** is,

$$X = \left[\frac{2 \epsilon V_B}{e (N_a + N_d)} \right]^{\frac{1}{2}} \left[\left(\frac{N_d}{N_a} \right)^{\frac{1}{2}} + \left(\frac{N_a}{N_d} \right)^{\frac{1}{2}} \right] \dots\dots\dots (22)$$

$$X = \left[\frac{2 \times 1.6 \times 10^{-19} \times 0.5}{1.6 \times 10^{-19} \times (10^{21} + 10^{21})} \right]^{\frac{1}{2}} \left[\left(\frac{10^{21}}{10^{21}} \right)^{\frac{1}{2}} + \left(\frac{10^{21}}{10^{21}} \right)^{\frac{1}{2}} \right] \dots\dots\dots (23)$$

⇒ Then we find that **Width (Thickness) of Junction Barrier** is,

$$\therefore X = 10^{-6} \text{ meter} \dots\dots\dots (24)$$

⇒ Now, if $N_d \gg N_a$, then we can neglect N_a in the Sum $((N_a + N_d))$ and also the term $\frac{N_a}{N_d}$ can be **approximated to zero**. The Equation (22) gives,

$$X = \left(\frac{2 \epsilon V_B}{e N_d} \right)^{\frac{1}{2}} \left(\frac{N_d}{N_a} \right)^{\frac{1}{2}} \dots\dots\dots (25)$$

$$X = \left(\frac{2 \epsilon V_B}{e N_a} \right)^{\frac{1}{2}} \dots\dots\dots (26)$$

❖ **V.V.I :-** Which shows that **Width of Space Charge Region Decreases** as the **Impurity Concentration Increases**.

⇒ Further, we find the ratio of **Potential Distribution in Space Charge Region on P – side V_1** and **Potential Distribution in Space Charge Region on N – side V_2 ,**

$$\frac{V_1}{V_2} = \left(\frac{X_1}{X_2} \right)^2 \left(\frac{N_a}{N_d} \right) \dots\dots\dots (27)$$

⇒ And we find the ratio of **Width of Space Charge Region in the P – side X_1** and **Width of Space Charge Region in the N – side X_2 ,**

$$\frac{X_1}{X_2} = \frac{N_d}{N_a} \dots\dots\dots (28)$$

⇒ Now from above two relations given in **Equation (27)** and **Equation (28)**, we find that,

$$\frac{V_1}{V_2} = \frac{N_d}{N_a} \dots\dots\dots (29)$$

❖ **V.V.I :-** We note here from above **Equation (29)** that, when $N_d \gg N_a$, $V_1 \gg V_2$ which **implies** that the **Potential Charge** is **confined to the region** which has **impurity in small amounts** (light doped).

(C) Junction Capacitance

⇒ The **Total Positive Charge in the N – type region** is equal to

$$= e N_d X_2 \text{ coulomb/meter}^2 \quad \text{and}$$

⇒ The **Total Negative Charge in the P – type region** is equal to

$$= - e N_a X_1 \text{ coulomb/meter}^2$$

⇒ But from **Equation (15)** from **Lecture – 5**,

$$N_a X_1 = N_d X_2 \quad \dots\dots\dots (15) \text{ From } \textbf{Lecture - 5}$$

⇒ On putting for X_1 , we find that $- e N_a X_1$ is equal to $+ e N_d X_2$ which implies that **Positive and Negative charge per meter²** have equal magnitude. The **Capacitance C per meter²** of the **Barrier/Depletion layer** is then given by,

$$C = \frac{d}{dV_B} (+ e N_d X_2) \quad \dots\dots\dots (30)$$

⇒ Now putting the value of X_2 of **Equation (18)** from **Lecture - 5** to the above **Equation (30)**, then we get,

$$C = \frac{d}{dV_B} \left[e N_d \left\{ \frac{2 \epsilon V_B}{e N_d \left(1 + \frac{N_d}{N_a} \right)} \right\}^{\frac{1}{2}} \right] \quad \dots\dots\dots (31)$$

$$\therefore C = \epsilon \left[\frac{e N_a N_d}{2 \epsilon V_B (N_a + N_d)} \right]^{\frac{1}{2}} \dots\dots\dots (32)$$

⇒ Now using **Equation (22)**, then we get **Junction Capacitance** as,

$$X = \left[\frac{2 \epsilon V_B}{e (N_a + N_d)} \right]^{\frac{1}{2}} \left[\left(\frac{N_d}{N_a} \right)^{\frac{1}{2}} + \left(\frac{N_a}{N_d} \right)^{\frac{1}{2}} \right] \dots\dots\dots (22)$$

$$\therefore C = \frac{\epsilon}{X} \dots\dots\dots (33)$$

❖ **Example :-** Consider a typical example with,

✦ $\epsilon = 8.85 \times 10^{-12} \times 16$ farad / meter (for Ge) and

✦ **Thickness of Junction Barrier** is, $X = 10^{-6}$ meter

$$\therefore C = \frac{\epsilon}{X} = \frac{8.85 \times 10^{-12} \times 16}{10^{-6}} = 144 \mu F / meter^2$$

⇒ In the next **Lecture - 7**, we will discuss the detailed of the **Barrier Potential in Terms of the Intrinsic Density of either Carrier (PART – 3)**.

to be continued
